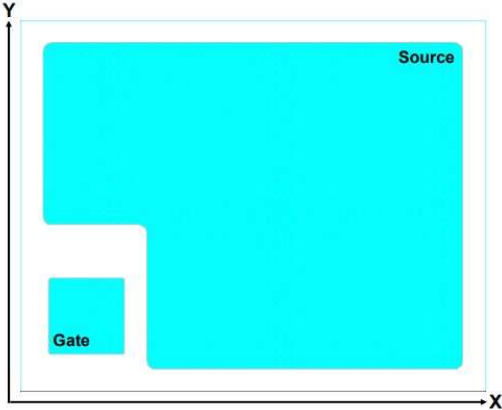


MOSFET Metal-Oxide-Semiconductor Field-Effect Transistor
20V N-Channel MOSFET

Bonding Pad Information	Chip Information	
	Die Size (with Scribe Line)	900μm x 730μm
	Gate Pad Size	140μm x 140μm
	Source Pad Size	Full metalized surface of source region
	Scribe Line Size	50μm
	Wafer Size	6inches
	Wafer Thickness	6mils
	Metallization	Front Side: Al/Si/Cu : 4μm
		Back Side: Ti/Ni/Ag : 1.4μm
	Recommended Wire Bonding	
	Gate Pad	1.65 mil x 1 (Cu wire)
	Source Pad	1.65 mil x 6 (Cu wire)
	Gross Die	23,950ea

Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±8	V
Operating Junction Temperature Range	T _J	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTIC						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{GS} =0V, V _{DS} =16V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	-	-	±10	uA
ON CHARACTERISTIC						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	0.5	-	1.1	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =2A	-	-	20	mΩ
		V _{GS} =2.5V, I _D =2A	-	-	25	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A	0.4	-	1.0	V

NOTE:

- The data tested by pulsed, pulse with ≤ 300us, duty cycle ≤ 2%.
- R_{DS(ON)} calculated by SOT-23 package type.
- ESD protected.